L Number	Hits	Search Text	DB	Time stamp
1	7654	((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/906) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:30
2	859	(((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/906) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:13
4	0	(((((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/906) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))) and transistor and gate and (source or drain)) and ((bilayer or (bi adj2 layer)) near5 resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:35
5	0	(((((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/906) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))) and transistor and gate and (source or drain)) and ((bilayer or (bi adj2 layer)) near10 resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:36
6	1	(((((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/906) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))) and transistor and gate and (source or drain)) and ((bilayer or (bi adj2 layer)) near10 photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:36
3	319	((((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/906) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))) and transistor and gate and (source or drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:51

8	0	(((((((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/906) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))) and transistor and gate and (source or drain)) and (selective$2 near10 deposit$3 near10 (insulat$3 or dielectric))) and (liquid adj phase adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:04
9	0	(((((((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/906) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))) and transistor and gate and (source or drain)) and (liquid adj phase adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:53
10	0	(((((((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/906) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))) and transistor and gate and (source or drain)) and ((liquid adj phase adj oxide) or lpod)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:53
7	13	(((((((438/637) or (438/639) or (438/640) or (438/641) or (438/666) or (438/669) or (438/671) or (438/672) or (438/762) or (438/765) or (438/770) or (438/771) or (438/772) or (438/774) or (438/782) or (438/787) or (438/906) or (438/947) or (438/948) or (438/949) or (438/950)).CCLS.) and (photoresist near10 (si or silicon or sylyated or silated))) and transistor and gate and (source or drain)) and (selective$2 near10 deposit$3 near10 (insulat$3 or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:13
11	242	(438/$.ccls. or 257/$.ccls.) and ((self adj aligned adj contact) or (borderless adj contact)) and bitline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:08
12	0	((438/$.ccls. or 257/$.ccls.) and ((self adj aligned adj contact) or (borderless adj contact)) and bitline) and (liquid adj phase adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:57
13	13	((438/$.ccls. or 257/$.ccls.) and ((self adj aligned adj contact) or (borderless adj contact)) and bitline) and (selective$2 near10 deposit$3 near10 (insulat$3 or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:04
14	255	(438/$.ccls. or 257/$.ccls.) and ((self adj aligned adj contact) or sac or (borderless adj contact)) and bitline	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:12

15	13	((438/$.ccls. or 257/$.ccls.) and ((self adj aligned adj contact) or sac or (borderless adj contact)) and bitline) not ((438/$.ccls. or 257/$.ccls.) and ((self adj aligned adj contact) or (borderless adj contact)) and bitline)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:09
16	2612	(438/$.ccls. or 257/$.ccls.) and ((self adj aligned adj contact) or sac or (borderless adj contact)) and (source or drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:57
17	121	((438/$.ccls. or 257/$.ccls.) and ((self adj aligned adj contact) or sac or (borderless adj contact)) and (source or drain)) and (selective$2 near10 deposit$3 near10 (insulat$3 or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:57
18	24	(((438/$.ccls. or 257/$.ccls.) and ((self adj aligned adj contact) or sac or (borderless adj contact)) and (source or drain)) and (selective$2 near10 deposit$3 near10 (insulat$3 or dielectric))) and (photoresist near10 (si or silicon or sylyated or silated))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:24
19	14	(("5429956") or ("5554557") or ("5565376") or ("5583358") or ("5696036") or ("5872041")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:56
20	329	((438/256) or (438/399)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:56
22	0	((((438/256) or (438/399)).CCLS.) and ((self adj aligned adj contact) or sac or (borderless adj contact)) and (source or drain)) and (selective$2 near10 deposit$3 near10 (insulat$3 or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:57
23	0	(((((438/256) or (438/399)).CCLS.) and ((self adj aligned adj contact) or sac or (borderless adj contact)) and (source or drain)) and (selective$2 near10 deposit$3 near10 (insulat$3 or dielectric))) and (liquid adj phase adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:57
24	0	((((438/256) or (438/399)).CCLS.) and ((self adj aligned adj contact) or sac or (borderless adj contact)) and (source or drain)) and (liquid adj phase adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:58
21	41	(((438/256) or (438/399)).CCLS.) and ((self adj aligned adj contact) or sac or (borderless adj contact)) and (source or drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:58

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